

1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

1.2 Features and benefits

- Low thermal resistance
- Fast switching

1.3 Applications

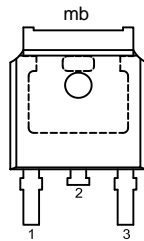
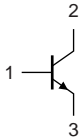
- Electronic lighting ballast
- DC-to-DC converters
- Inverters
- Motor control systems

1.4 Quick reference data

- $V_{CESM} \leq 700 \text{ V}$
- $I_C \leq 8 \text{ A}$
- $P_{tot} \leq 80 \text{ W}$
- $h_{FEsat} = 11 \text{ (typ)}$

2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Symbol |
|-----|---------------------------------------|---|---|
| 1 | base |  <p style="text-align: center;">mb</p> <p style="text-align: center;">1 2 3</p> <p style="text-align: center;">DPAK (SOT428)</p> |  <p style="text-align: center;">sym056</p> |
| 2 | collector [1] | | |
| 3 | emitter | | |
| mb | mounting base; connected to collector | | |

[1] It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.

3. Ordering information

Table 2. Ordering information

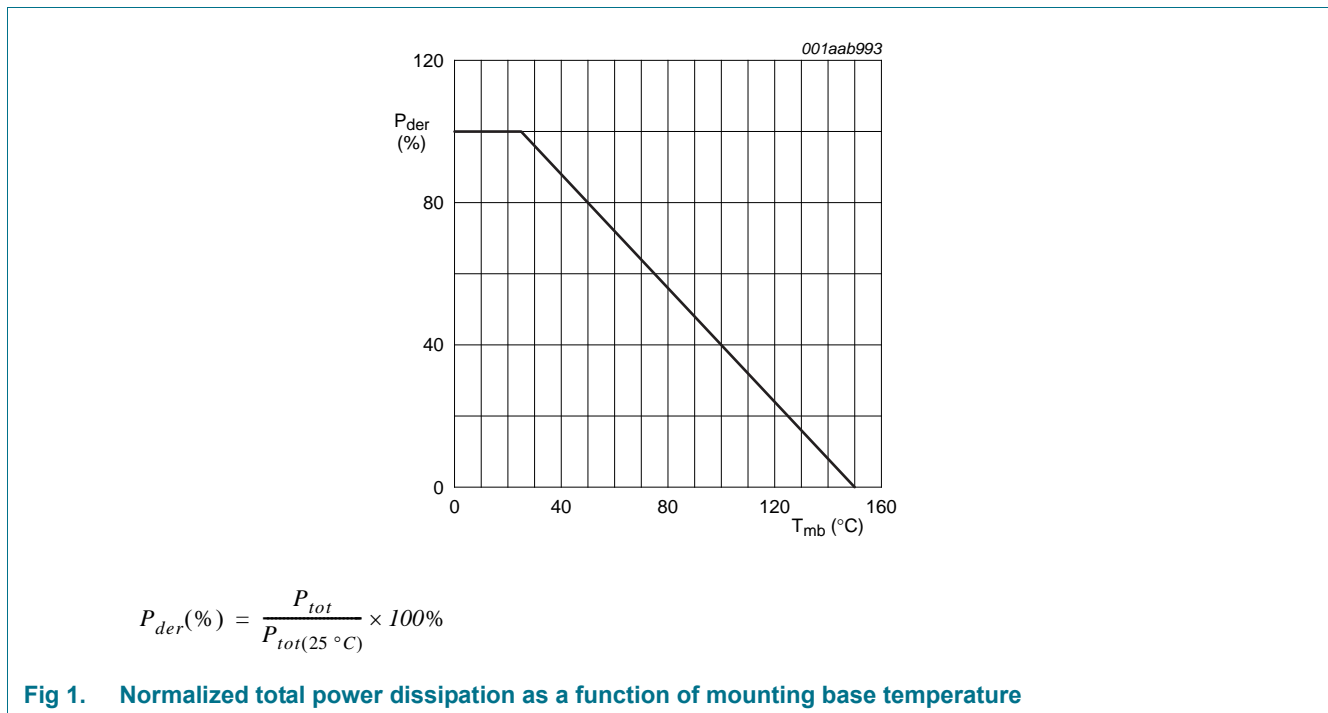
| Type number | Package | | Version |
|-------------|---------|--|---------|
| | Name | Description | |
| BUJ105AD | D-PAK | plastic single-ended surface mounted package; 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------|--------------------------------|---|-----|------|------|
| V_{CESM} | peak collector-emitter voltage | $V_{BE} = 0\text{ V}$ | - | 700 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 400 | V |
| V_{CBO} | collector-base voltage | open emitter | - | 700 | V |
| I_C | collector current (DC) | | - | 8 | A |
| I_{CM} | peak collector current | | - | 16 | A |
| I_B | base current (DC) | | - | 4 | A |
| I_{BM} | peak base current | | - | 8 | A |
| P_{tot} | total power dissipation | $T_{mb} = \leq 25\text{ °C}$; see Figure 1 | - | 80 | W |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| T_j | junction temperature | | - | 150 | °C |



5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 2 | - | - | 1.56 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | | [1] | 75 | - | K/W |

[1] Device mounted on a printed-circuit board; minimum footprint

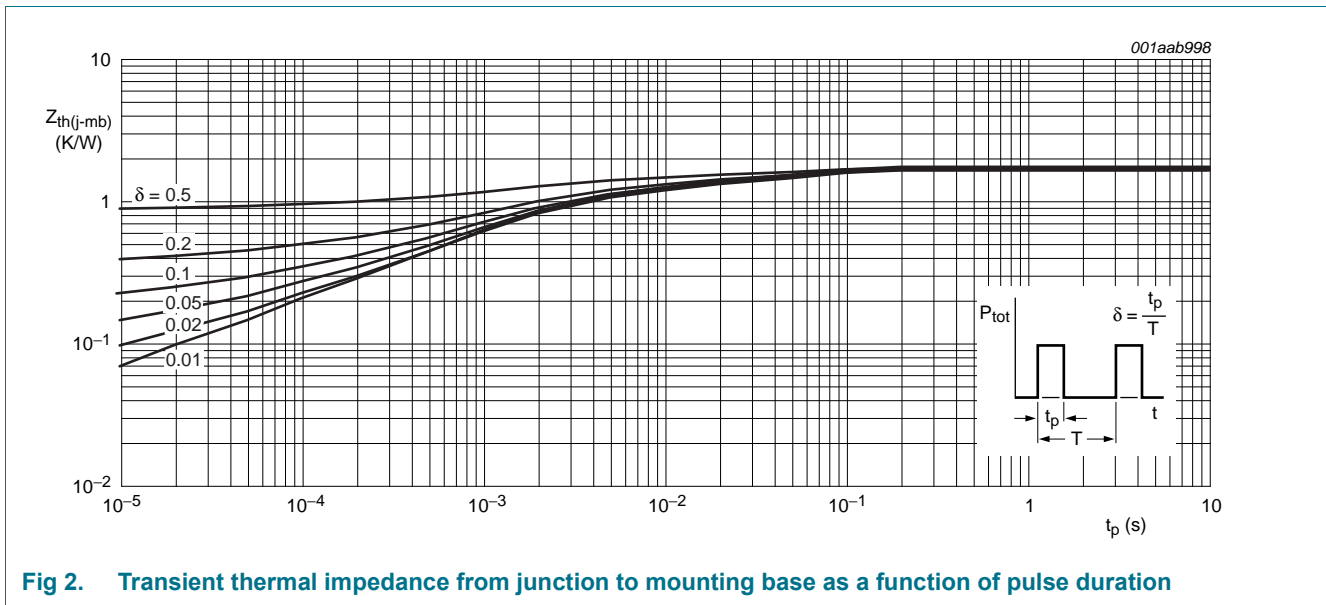


Fig 2. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5. Characteristics

$T_{mb} = 25\text{ }^\circ\text{C}$; unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|-----|------|
| Static characteristics | | | | | | |
| I_{CES} | collector-emitter cut-off current | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ | [1] | - | 0.2 | mA |
| | | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}; T_j = 125\text{ }^\circ\text{C}$ | [1] | - | 0.5 | mA |
| I_{CBO} | collector-base cut-off current | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ | [1] | - | 0.2 | mA |
| I_{CEO} | collector-emitter cut-off current | $V_{CEO} = V_{CEOMmax} = 400\text{ V}$ | [1] | - | 0.1 | mA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ | - | - | 1 | mA |
| V_{CE0sus} | collector-emitter sustaining voltage | $I_B = 0\text{ A}; I_C = 10\text{ mA}; L = 25\text{ mH}$; see Figure 3 and 4 | 400 | - | - | V |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 4.0\text{ A}; I_B = 0.8\text{ A}$; see Figure 11 | - | 0.3 | 1.0 | V |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 4.0\text{ A}; I_B = 0.8\text{ A}$; see Figure 12 | - | 1.0 | 1.5 | V |
| h_{FE} | DC current gain | $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$ | 10 | 14 | 34 | |
| | | $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$; see Figure 10 | 13 | 23 | 36 | |
| h_{FEsat} | DC saturation current gain | $I_C = 4.0\text{ A}; V_{CE} = 5\text{ V}$ | 8 | 11 | 15 | |

Table 5. Characteristics ...continued
 $T_{mb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|--------------|--|-----|------|-----|---------------|
| Dynamic characteristics | | | | | | |
| Switching times (resistive load); see Figure 5 and 6 | | | | | | |
| t_{on} | turn-on time | $I_{Con} = 5\text{ A}$; $I_{Bon} = -I_{Boff} = 1\text{ A}$; $R_L = 75\ \Omega$ | - | 0.65 | 1 | μs |
| t_{stg} | storage time | | - | 1.8 | 2.5 | μs |
| t_f | fall time | | - | 0.3 | 0.5 | μs |
| Switching times (inductive load); see Figure 7 and 8 | | | | | | |
| t_{stg} | storage time | $I_{Con} = 5\text{ A}$; $I_{Bon} = 1\text{ A}$; $L_B = 1\ \mu\text{H}$; | - | 1.2 | 1.7 | μs |
| t_f | fall time | $V_{BB} = -5\text{ V}$ | - | 20 | 50 | ns |
| Switching times (inductive load); see Figure 7 and 8 | | | | | | |
| t_{stg} | storage time | $I_{Con} = 5\text{ A}$; $I_{Bon} = 1\text{ A}$; $L_B = 1\ \mu\text{H}$; | - | 1.4 | 1.9 | μs |
| t_f | fall time | $V_{BB} = -5\text{ V}$; $T_j = 100\text{ }^{\circ}\text{C}$ | - | 25 | 100 | ns |

[1] Measured with half sine-wave voltage (curve tracer).

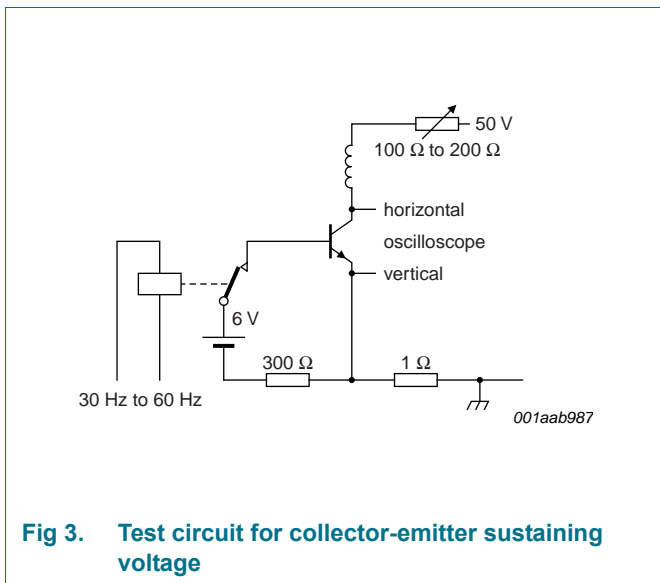


Fig 3. Test circuit for collector-emitter sustaining voltage

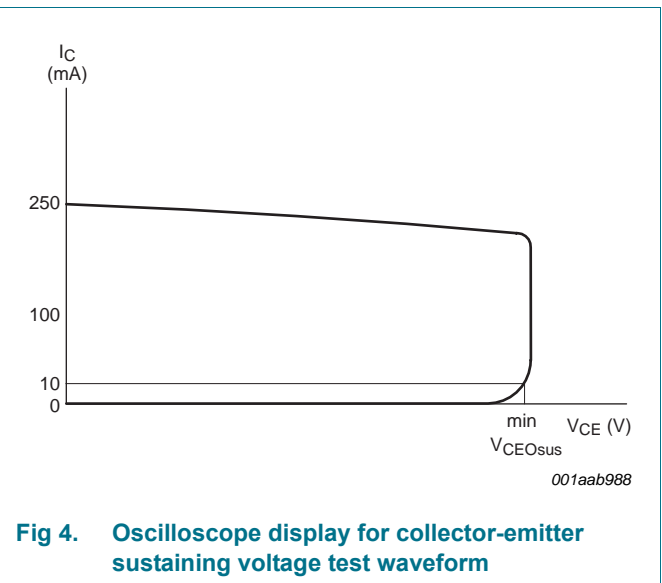
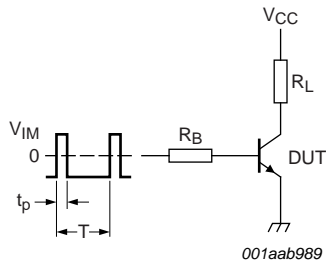


Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



$V_{IM} = -6\text{ V to }+8\text{ V}; V_{CC} = 250\text{ V}; t_p = 20\text{ }\mu\text{s};$
 $\delta = t_p/T = 0.01.$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

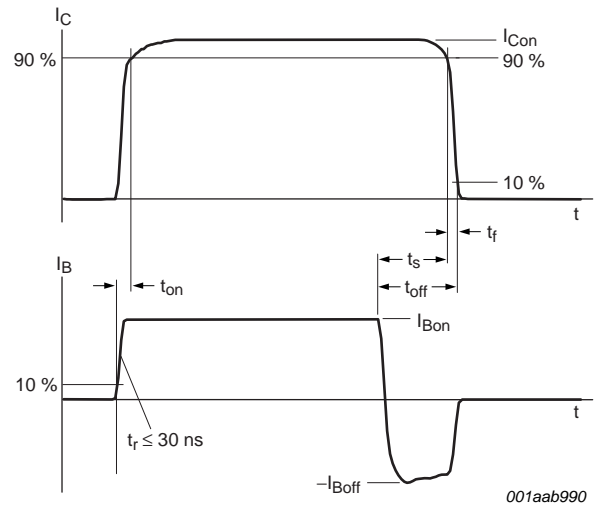
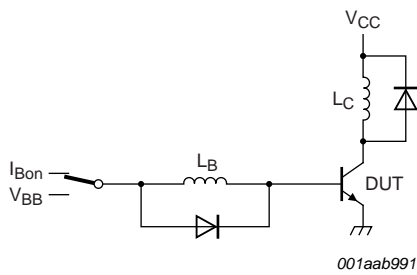


Fig 6. Switching times waveforms for resistive load



$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\text{ }\mu\text{H}; L_B = 1\text{ }\mu\text{H}.$

Fig 7. Test circuit for inductive load switching

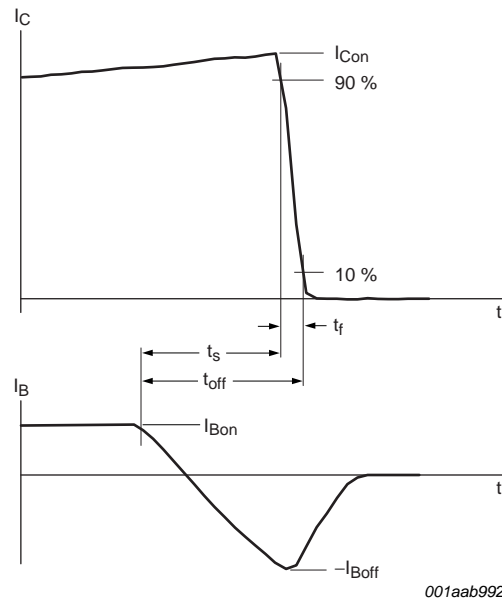


Fig 8. Switching times waveforms for inductive load

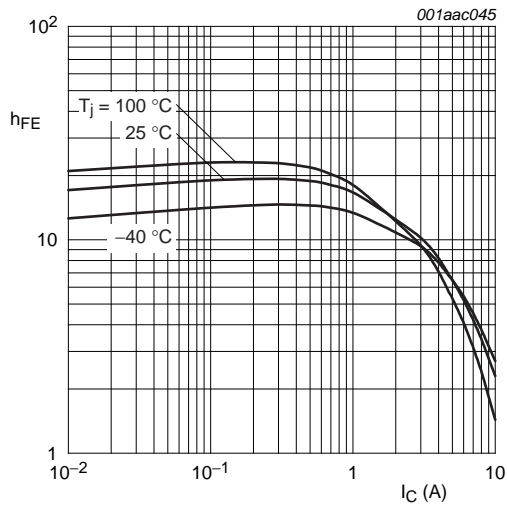


Fig 9. DC current gain as a function of collector current; typical values at $V_{CE} = 1\text{ V}$

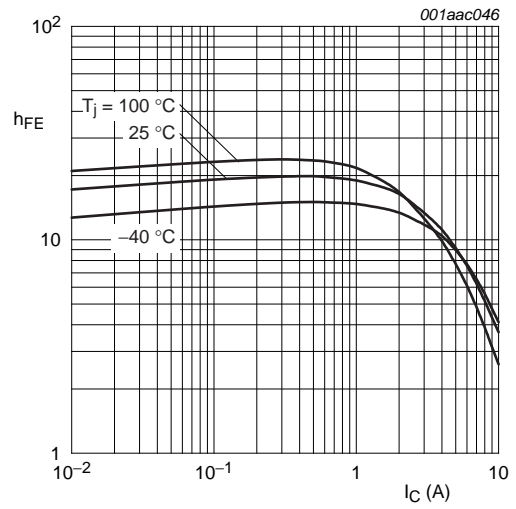
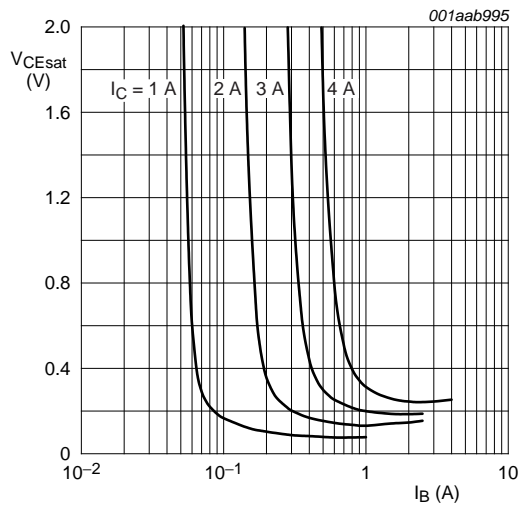
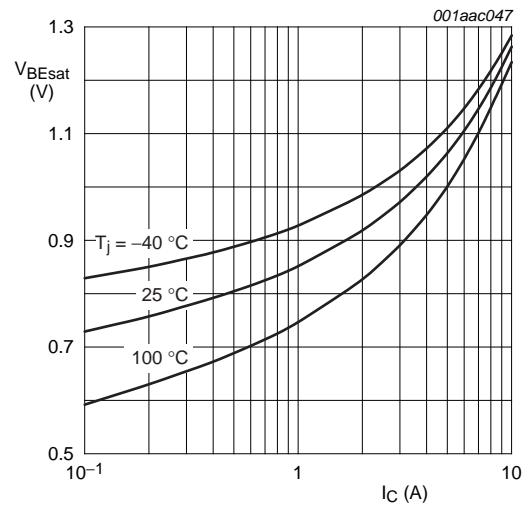


Fig 10. DC current gain as a function of collector current; typical values at $V_{CE} = 5\text{ V}$



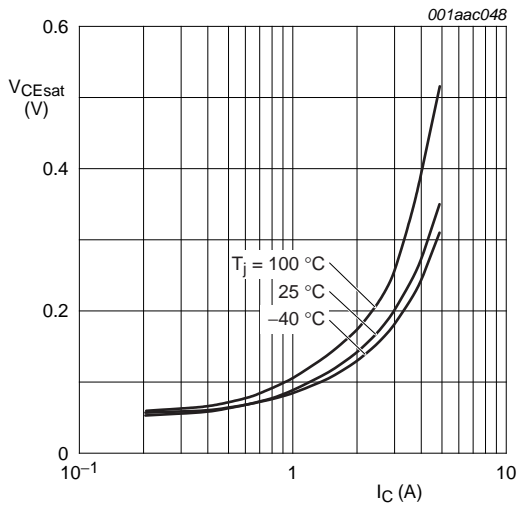
$T_j = 25\text{ °C}$.

Fig 11. Collector-emitter saturation voltage as a function of base current; typical values



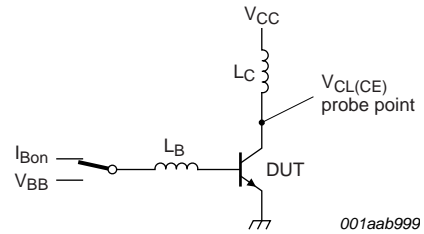
$I_C/I_B = 4$.

Fig 12. Base-emitter saturation voltage as a function of collector current; typical values



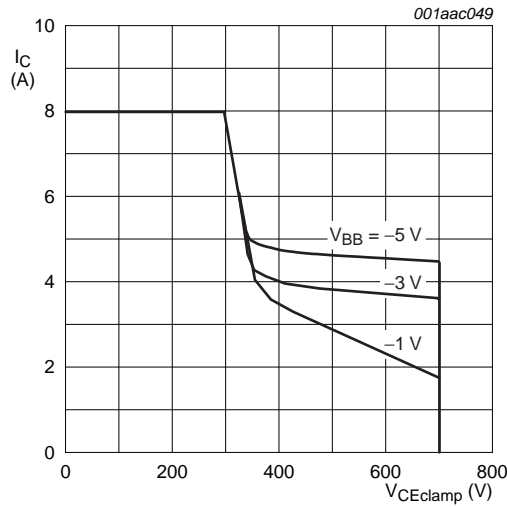
$I_C/I_B = 4$.

Fig 13. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CEclamp} < 700\text{ V}$; $V_{CC} = 150\text{ V}$; $V_{BB} = -5\text{ V}$, -3 V and -1 V ; $L_B = 1\ \mu\text{H}$; $L_C = 200\ \mu\text{H}$.

Fig 14. Test circuit for reverse bias safe operating area



$T_j < T_{j(max)}$.

Fig 15. Reverse bias safe operating area

7. Package information

Epoxy meets requirements of UL94 V-0 at $1/8$ inch.

8. Package outline

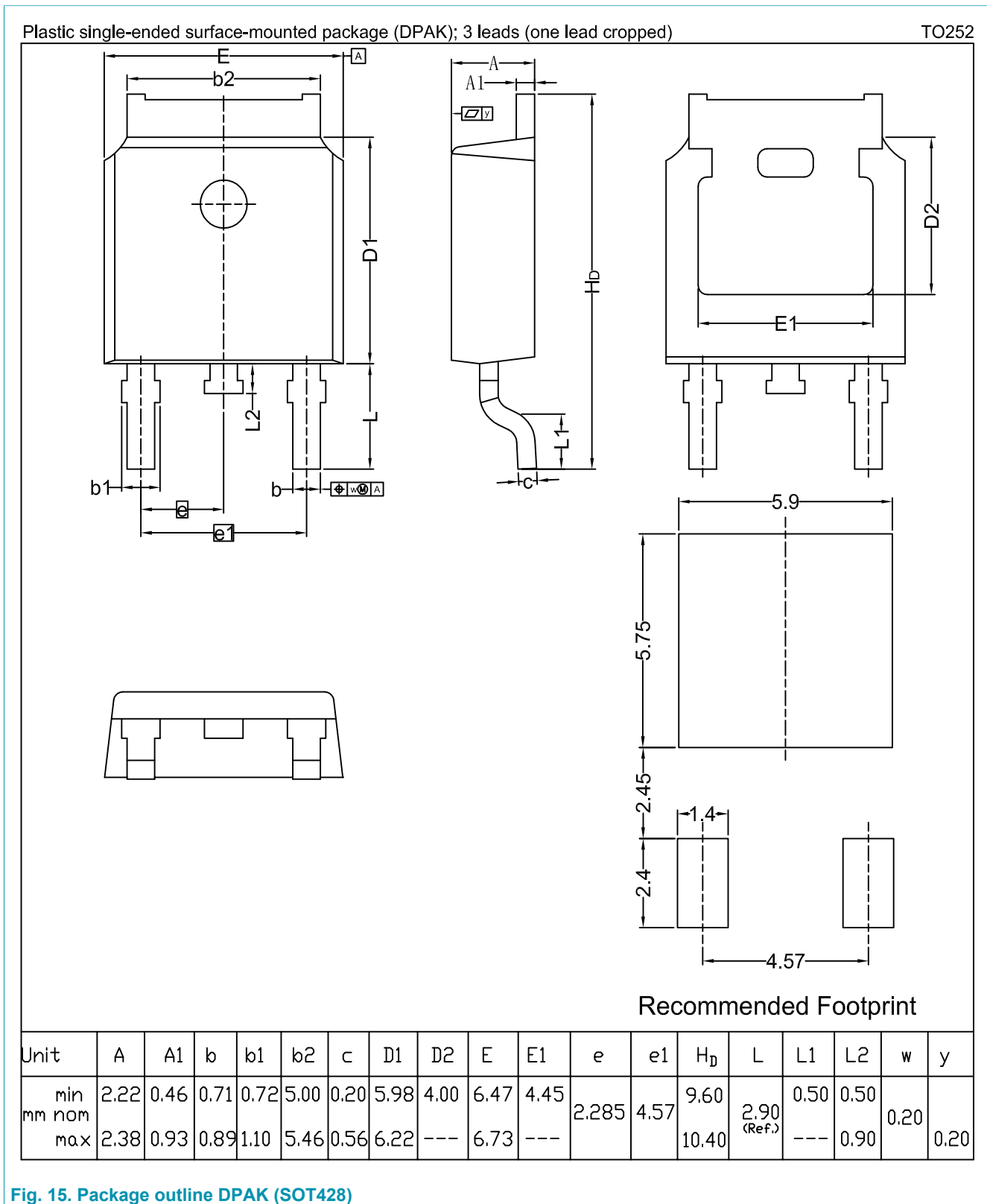


Fig. 15. Package outline DPAK (SOT428)

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